UMW FDS6675

-30V P-Channel MOSFET

1.Description

These devices are well suited for notebook computer applications: load switching and power management, battery charging circuits, and DC/DC conversion.

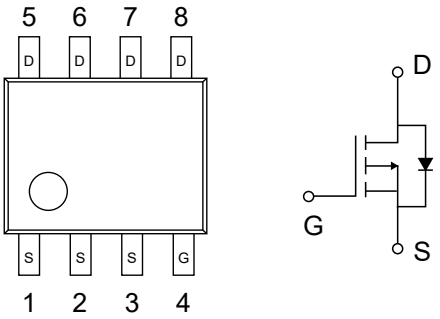
2.Features

- $V_{DS\ (V)}$=-30V
- I_D=-11A(V_{GS}=-10)
- $R_{DS(ON)}$<14mΩ(V_{GS}=10V)
- $R_{DS(ON)}$<20mΩ(V_{GS}=4.5V)

3.Pinning information

Pin	Symbol	Description
4	G	GATE
1,2,3	S	SOURCE
5,6,7,8	D	DRAIN

SOP-8



4.Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Value	Units
Drain-Source Voltage		V_{DSS}	-30	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current – Continuous		I_D	-11	A
– Pulsed	(Note 1a)		-50	
Power Dissipation for Single Operation	(Note 1a)	P_D	2.5	W
	(Note 1b)		1.2	
	(Note 1c)		1	
Storage Junction Temperature Range		T_J, T_{STG}	-55 to 150	°C

5.Thermal Characteristics

Parameter	Symbol	Rating	Units
Thermal Resistance, Junction-to-Ambient (Note 1a)	$R_{\theta JA}$	50	°C/W
Thermal Resistance, Junction-to-Case (Note 1)	$R_{\theta JC}$	25	°C/W

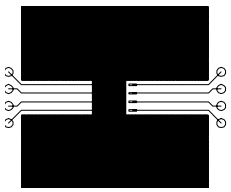
6.Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	I_D=-250μA, V_{GS}=0V	-30			V
Breakdown Voltage Temperature Coefficient	$\frac{\Delta BV_{DSS}}{\Delta T_J}$	I_D=-250μA Referenced to 25°C		-22		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-24V, V_{GS}=0V			-1	μA
		T_J=55°C			-10	μA
Gate–Body Leakage, Forward	I_{GSSF}	V_{GS}=20V, V_{DS}=0V			100	nA
Gate–Body Leakage, Reverse	I_{GSSR}	V_{GS}=-20V, V_{DS}=0V			-100	nA
On Characteristics (Note 2)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.5	-2	V
Gate Threshold Voltage Temp. Coefficien	$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	I_D=250μA Referenced to 25°C		4.3		mV/°C
Static Drain–Source On–Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-11A		11	14	mΩ
		V_{GS}=-4.5V, I_D=-9A		15	20	mΩ
On–State Drain Current	$I_{D(ON)}$	V_{GS}=-10V, V_{DS}=-5V	-50			A
Forward Transconductance	g_{FS}	V_{DS}=-10V, I_D=-11A		32		S
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS}=-15V		3000		pF
Output Capacitance	C_{oss}	V_{GS}=0V		870		pF
Reverse Transfer Capacitance	C_{rss}	f =1MHz		360		pF
SWITCHING PARAMETERS (Note 2)						
Turn-On DelayTime	$t_{D(on)}$			12	22	ns
Turn-On Rise Time	t_r	V_{DS}=-15V, I_D=-1A		16	27	ns
Turn-Off DelayTime	$t_{D(off)}$	V_{GEN}=-10V, R_{GEN}=6Ω		50	80	ns
Turn-Off Fall Time	t_f			100	140	ns

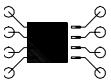
Total Gate Charge	Q_g	V_{DS}=-15V, I_D=-11A V_{GS}=-5V		30	42	nC
Gate–Source Charge	Q_{gs}			9		nC
Gate–Drain Charge	Q_{gd}			11		nC
Drain-Source Diode Characteristics						
Maximum Continuous Drain-Source Diode Forward Current	I_S				-2.1	A
Drain-Source Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=-2.1A(Note 2)		-0.72	-1.2	V

Notes:

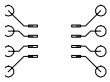
1. $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design.



a) 50° C/W when mounted on a 0.5 in ^{2} pad of 2 oz. copper.



b) 105° C/W when mounted on a 0.02 in ^{2} pad of 2 oz. copper.

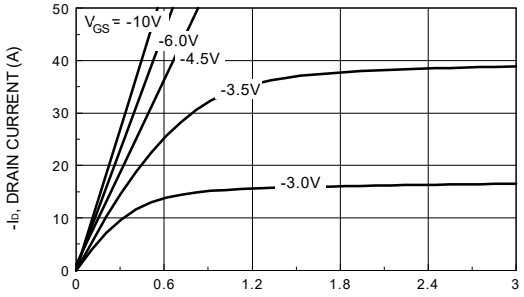


c) 125° C/W when mounted on a 0.003 in ^{2} pad of 2 oz. copper.

Scale 1 : 1 on letter size paper

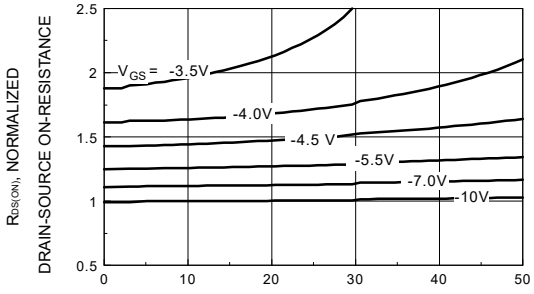
2. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

7.1TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



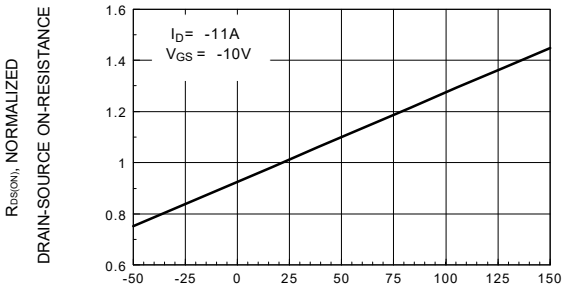
-$V_{DS,}$ DRAIN TO SOURCE VOLTAGE (V)

Fig 1: On-Region Characteristics.



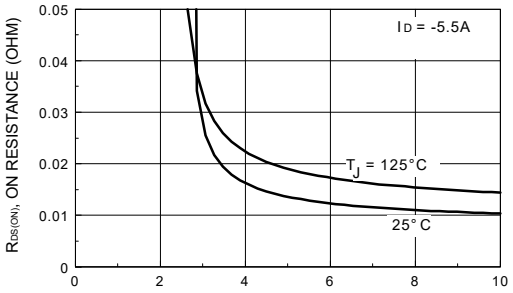
-I_D, DRAIN CURRENT (A)

Figure 2: On-Resistance Variation with Drain Current and Gate Voltage.



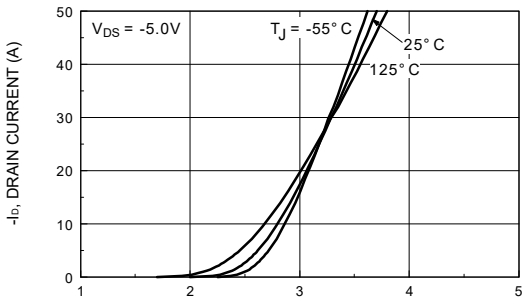
T_J, JUNCTION TEMPERATURE (°C)

Figure 3: On-Resistance Variation with Temperature.



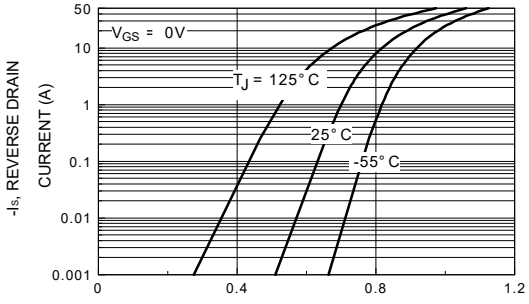
-V_{GS}, GATE TO SOURCE VOLTAGE (V)

Figure 4: On-Resistance Variation with Gate-to-Source Voltage.



-V_{GS}, GATE TO SOURCE VOLTAGE (V)

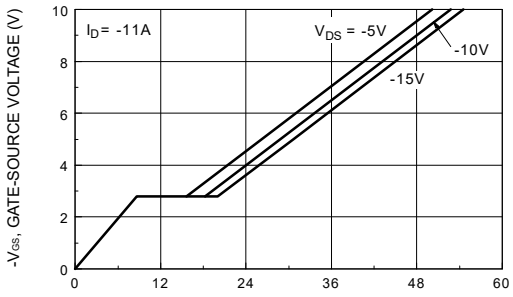
Figure 5: Transfer Characteristics.



-V_{SD}, BODY DIODE VOLTAGE (V)

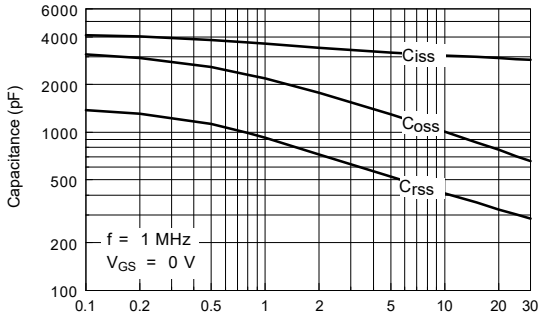
Figure 6: . Body Diode Forward Voltage Variation with Source Current and Temperature.

7.2TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS



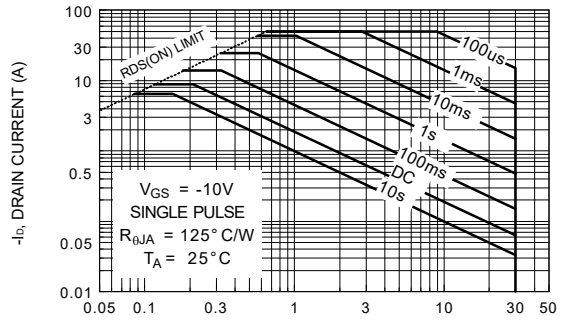
Q_g, GATE CHARGE (nC)

Figure 7: Gate-Charge Characteristics



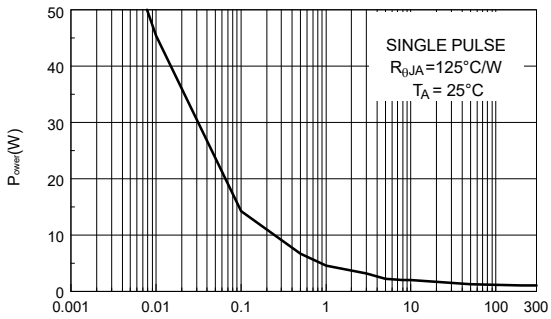
-V_{DS}, DRAIN TO SOURCE VOLTAGE (V)

Figure 8: Capacitance Characteristics



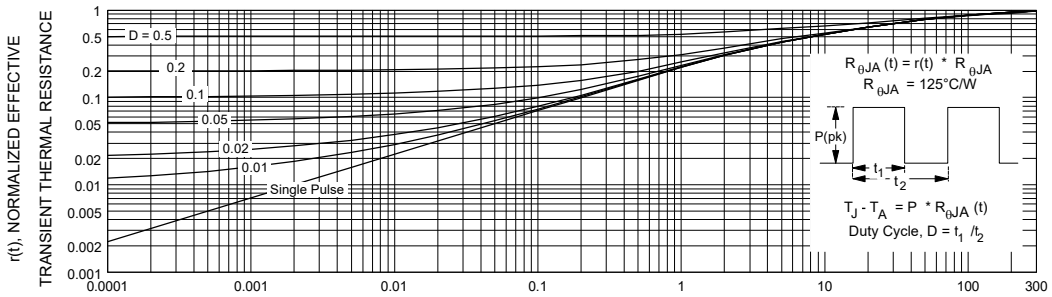
-V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 9: Maximum Safe Operating Area.



SINGLE PULSE TIME (SEC)

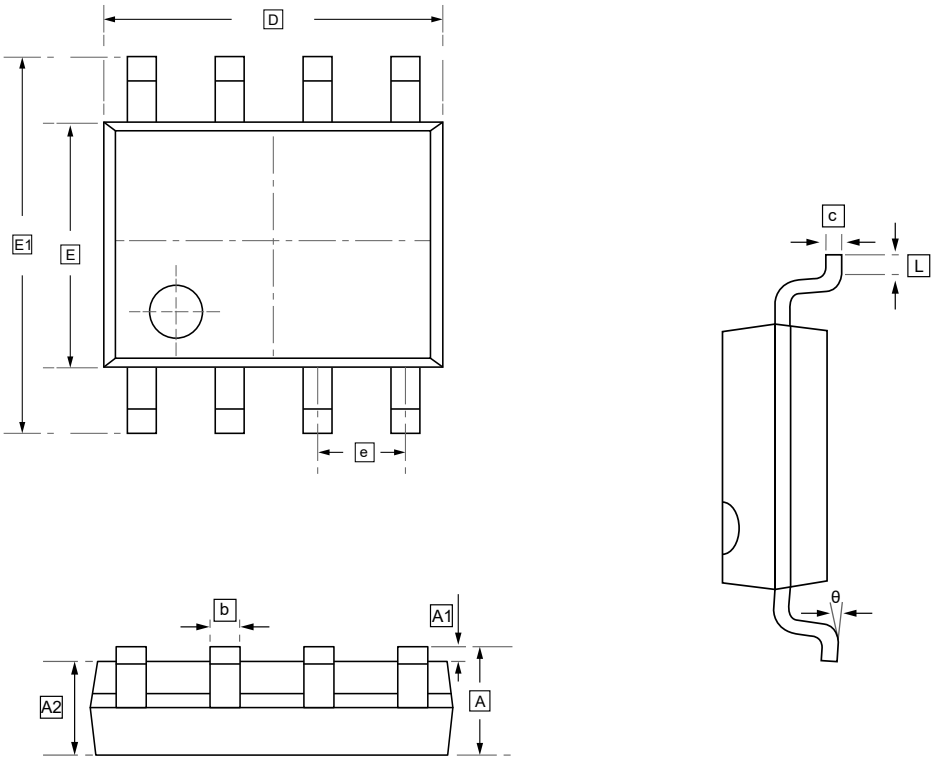
Figure 10: Single Pulse Maximum Power Dissipation.



t,TIME (sec)

Figure 11: Transient Thermal Response Curve.

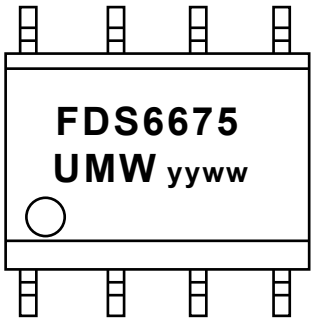
8.SOP-8 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	A1	A2	b	c	D	E	E1	e	L	θ
Min	1.350	0.000	1.350	0.330	0.170	4.700	3.800	5.800	1.270	0.400	0°
Max	1.750	0.100	1.550	0.510	0.250	5.100	4.000	6.200	BSC	1.270	8°

9.Ordering information



yy: Year Code
ww: Week Code

Order Code	Package	Base QTY	Delivery Mode
UMW FDS6675	SOP-8	3000	Tape and reel

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